

# DATA SHEET

**BFQ67W**

**NPN 8 GHz wideband transistor**

Product specification

September 1995



# NPN 8 GHz wideband transistor

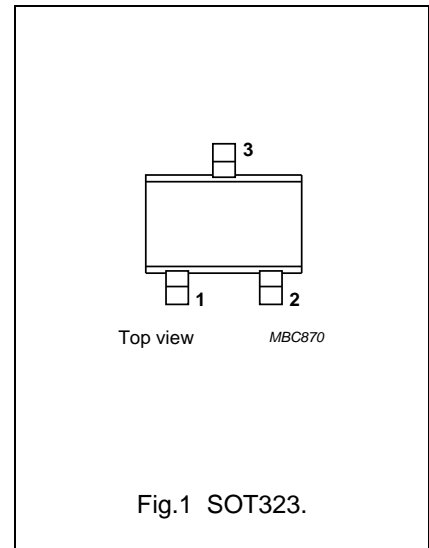
# BFQ67W

## FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability
- SOT323 envelope.

## PINNING

PIN	DESCRIPTION
Code: V2	
1	base
2	emitter
3	collector



## DESCRIPTION

NPN transistor in a plastic SOT323 envelope.

It is designed for wideband applications such as satellite TV tuners and RF portable communications equipment up to 2 GHz.

## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–	20	V
$V_{CEO}$	collector-emitter voltage	open base	–	–	10	V
$I_C$	DC collector current		–	–	50	mA
$P_{tot}$	total power dissipation	up to $T_s = 118\text{ °C}$ ; note 1	–	–	300	mW
$h_{FE}$	DC current gain	$I_C = 15\text{ mA}$ ; $V_{CE} = 5\text{ V}$ ; $T_j = 25\text{ °C}$	60	100	–	
$f_T$	transition frequency	$I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	–	8	–	GHz
$G_{UM}$	maximum unilateral power gain	$I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 1\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	–	13	–	dB
F	noise figure	$I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 1\text{ GHz}$	–	1.3	–	dB

## LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	20	V
$V_{CEO}$	collector-emitter voltage	open base	–	10	V
$V_{EBO}$	emitter-base voltage	open collector	–	2.5	V
$I_C$	DC collector current		–	50	mA
$P_{tot}$	total power dissipation	up to $T_s = 118\text{ °C}$ ; note 1	–	300	mW
$T_{stg}$	storage temperature		–65	150	°C
$T_j$	junction temperature		–	175	°C

## Note

1.  $T_s$  is the temperature at the soldering point of the collector tab.

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## THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 118\text{ °C}$ ; note 1	190 K/W

## Note

- $T_s$  is the temperature at the soldering point of the collector tab.

## CHARACTERISTICS

$T_j = 25\text{ °C}$ , unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0$ ; $V_{CB} = 5\text{ V}$	–	–	50	nA
$h_{FE}$	DC current gain	$I_C = 15\text{ mA}$ ; $V_{CE} = 5\text{ V}$	60	100	–	
$C_c$	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = 8\text{ V}$ ; $f = 1\text{ MHz}$	–	0.7	–	pF
$C_e$	emitter capacitance	$I_C = i_c = 0$ ; $V_{EB} = 0.5\text{ V}$ ; $f = 1\text{ MHz}$	–	1.3	–	pF
$C_{re}$	feedback capacitance	$I_C = 0$ ; $V_{CB} = 8\text{ V}$ ; $f = 1\text{ MHz}$	–	0.5	–	pF
$f_T$	transition frequency	$I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	–	8	–	GHz
$G_{UM}$	maximum unilateral power gain (note 1)	$I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 1\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	–	13	–	dB
		$I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	–	8	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}$ ; $I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 1\text{ GHz}$	–	1.3	–	dB
		$\Gamma_s = \Gamma_{opt}$ ; $I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 1\text{ GHz}$	–	2	–	dB
		$\Gamma_s = \Gamma_{opt}$ ; $I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$	–	2.2	–	dB
		$I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$ ; $Z_s = 60\ \Omega$	–	2.5	–	dB
		$\Gamma_s = \Gamma_{opt}$ ; $I_C = 15\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$	–	2.7	–	dB
		$I_C = 5\text{ mA}$ ; $V_{CE} = 8\text{ V}$ ; $f = 2\text{ GHz}$ ; $Z_s = 60\ \Omega$	–	3	–	dB

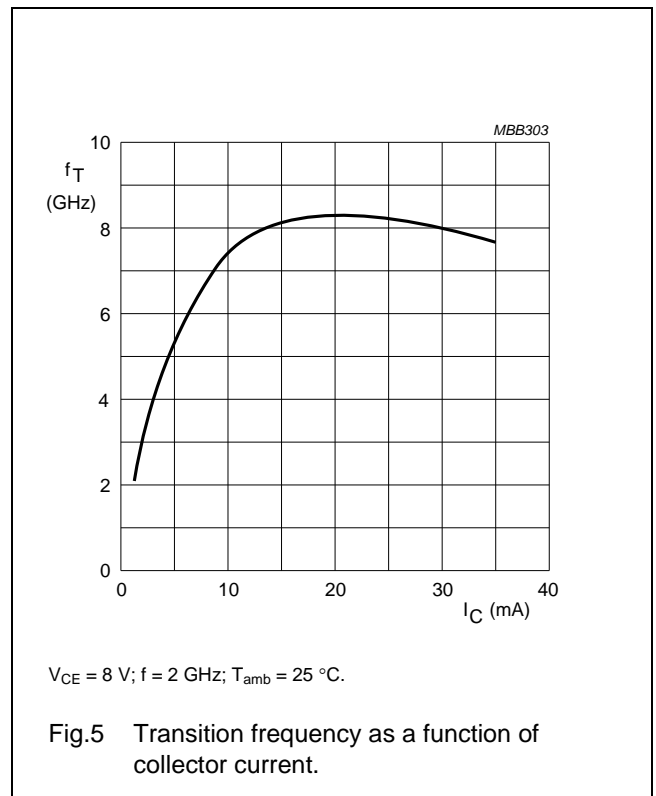
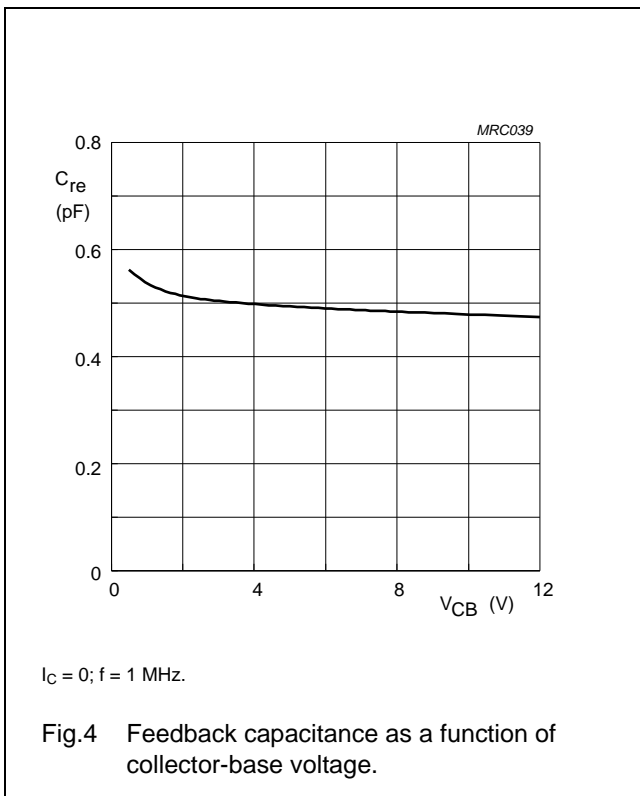
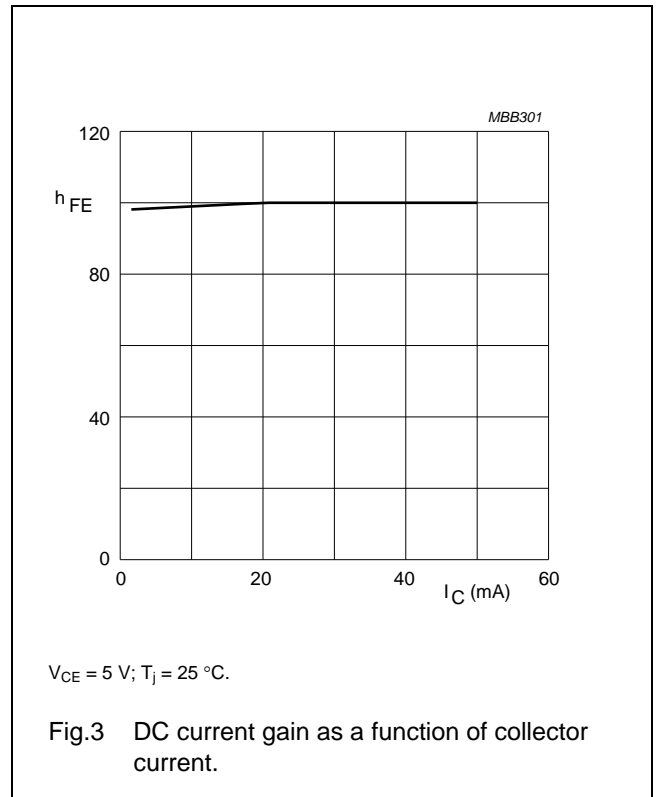
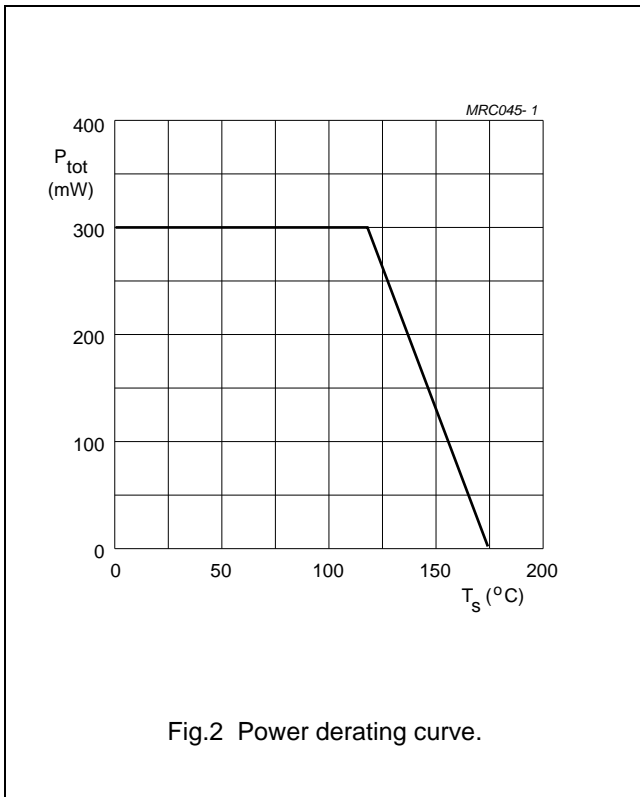
## Note

- $G_{UM}$  is the maximum unilateral power gain, assuming  $S_{12}$  is zero and

$$G_{UM} = 10 \log \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)} \text{ dB.}$$

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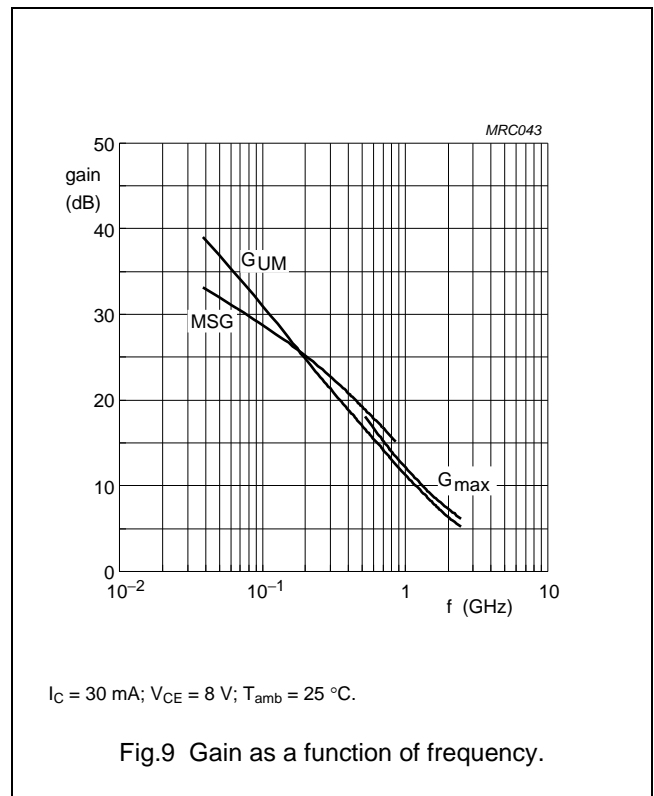
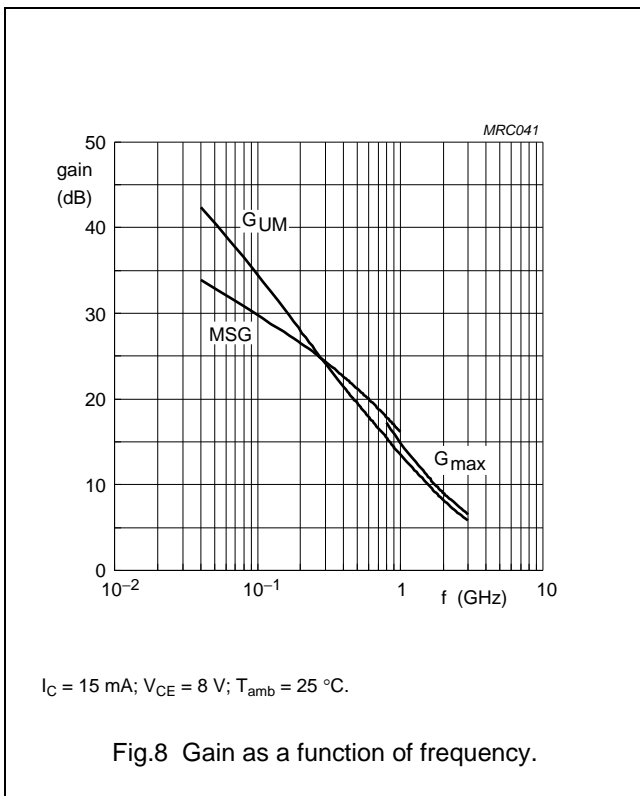
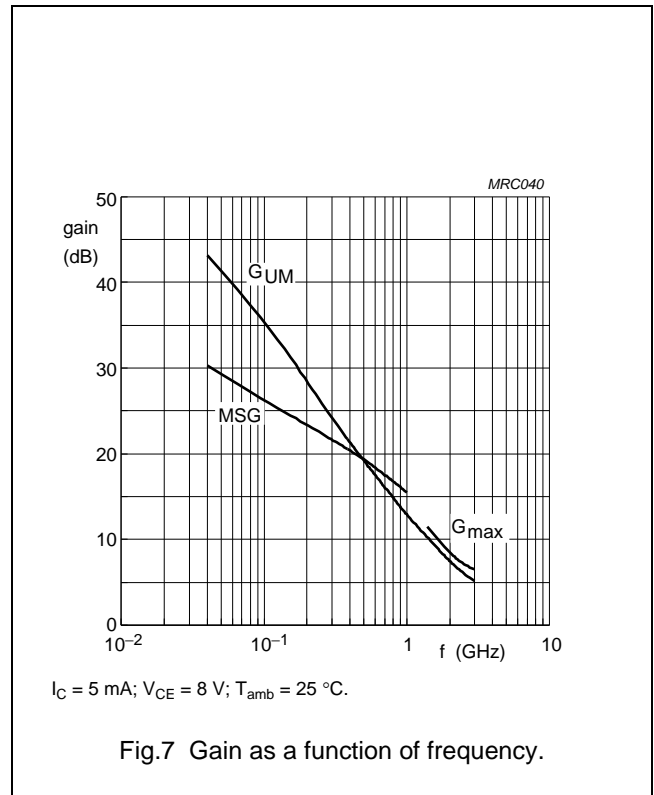
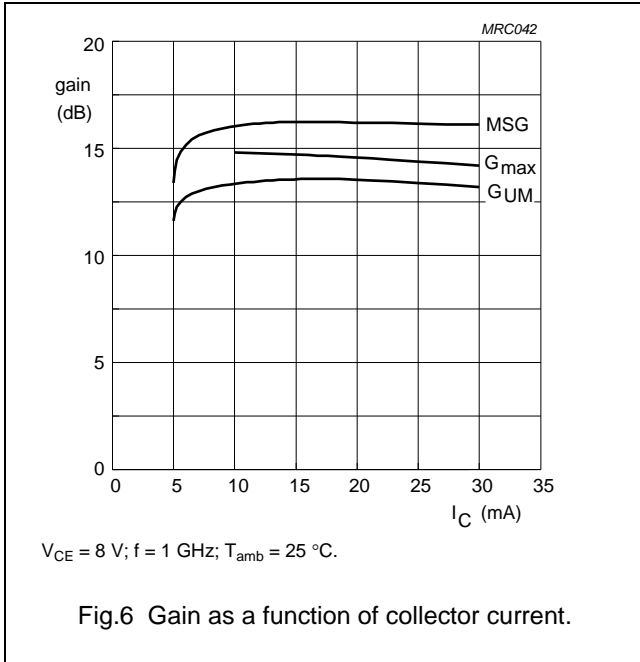
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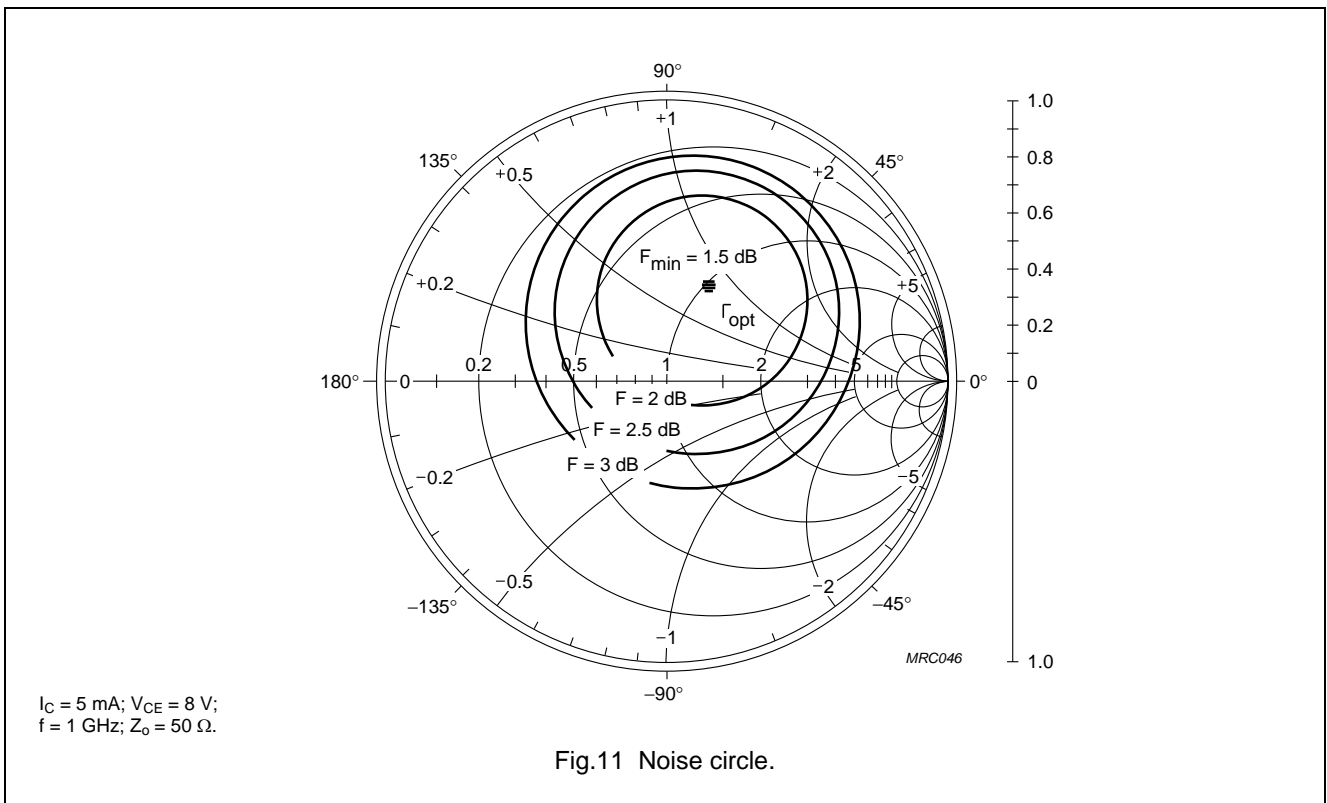
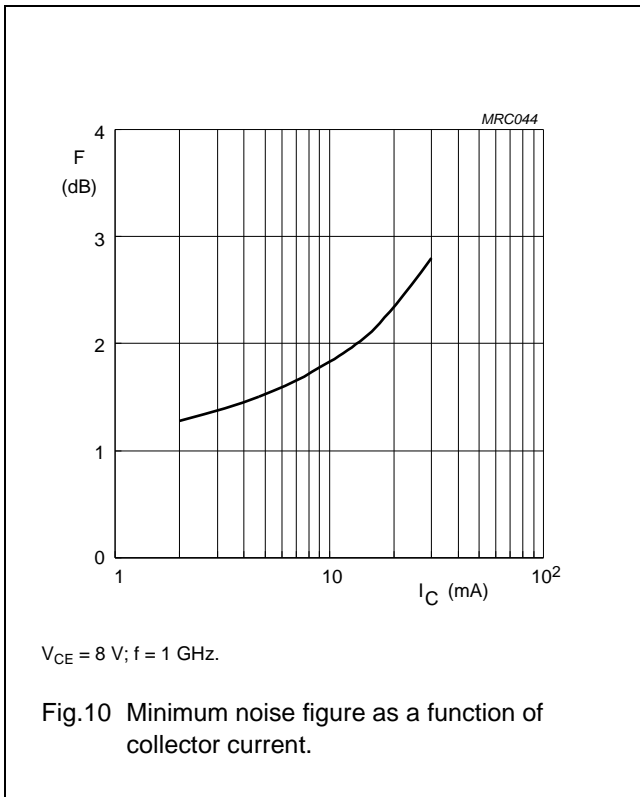
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In Figs 6 to 9,  $G_{UM}$  = maximum unilateral power gain;  
 MSG = maximum stable gain;  $G_{max}$  = maximum available gain.



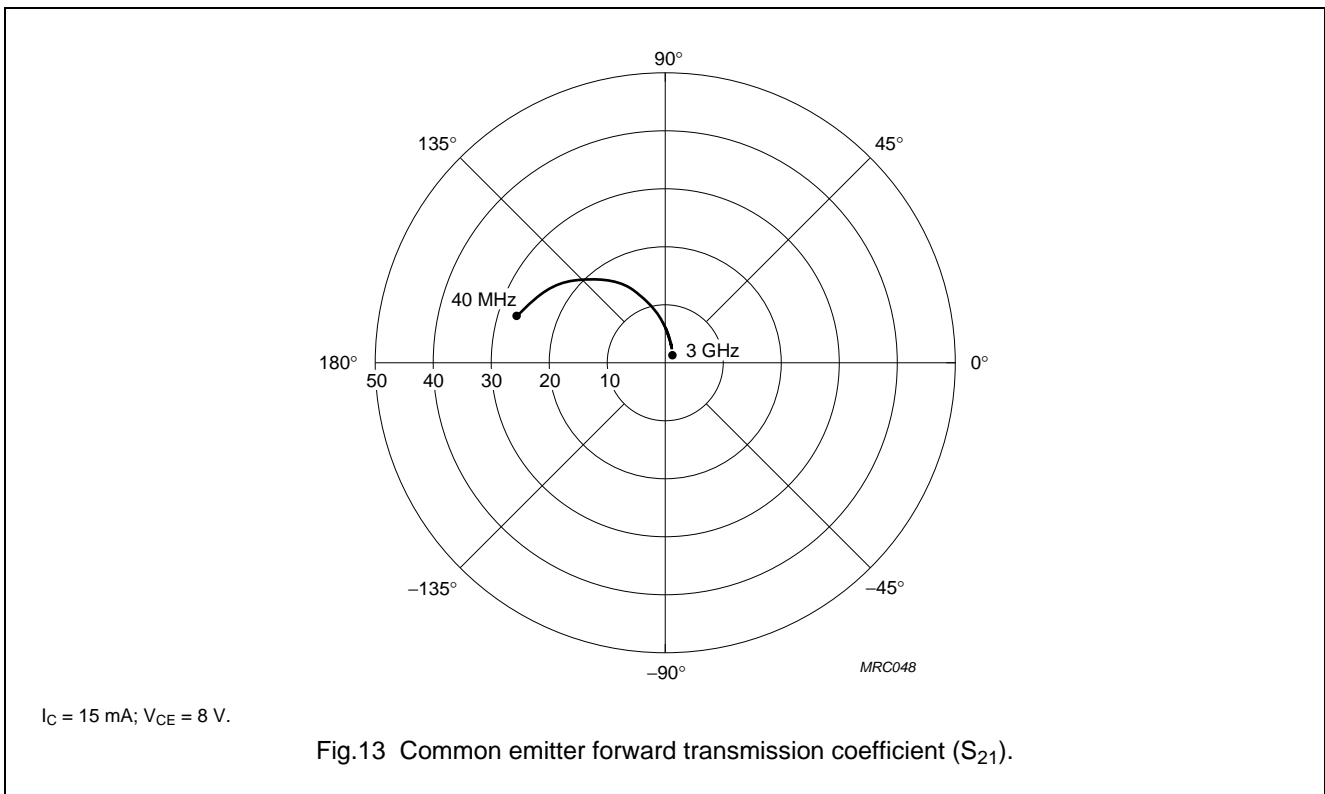
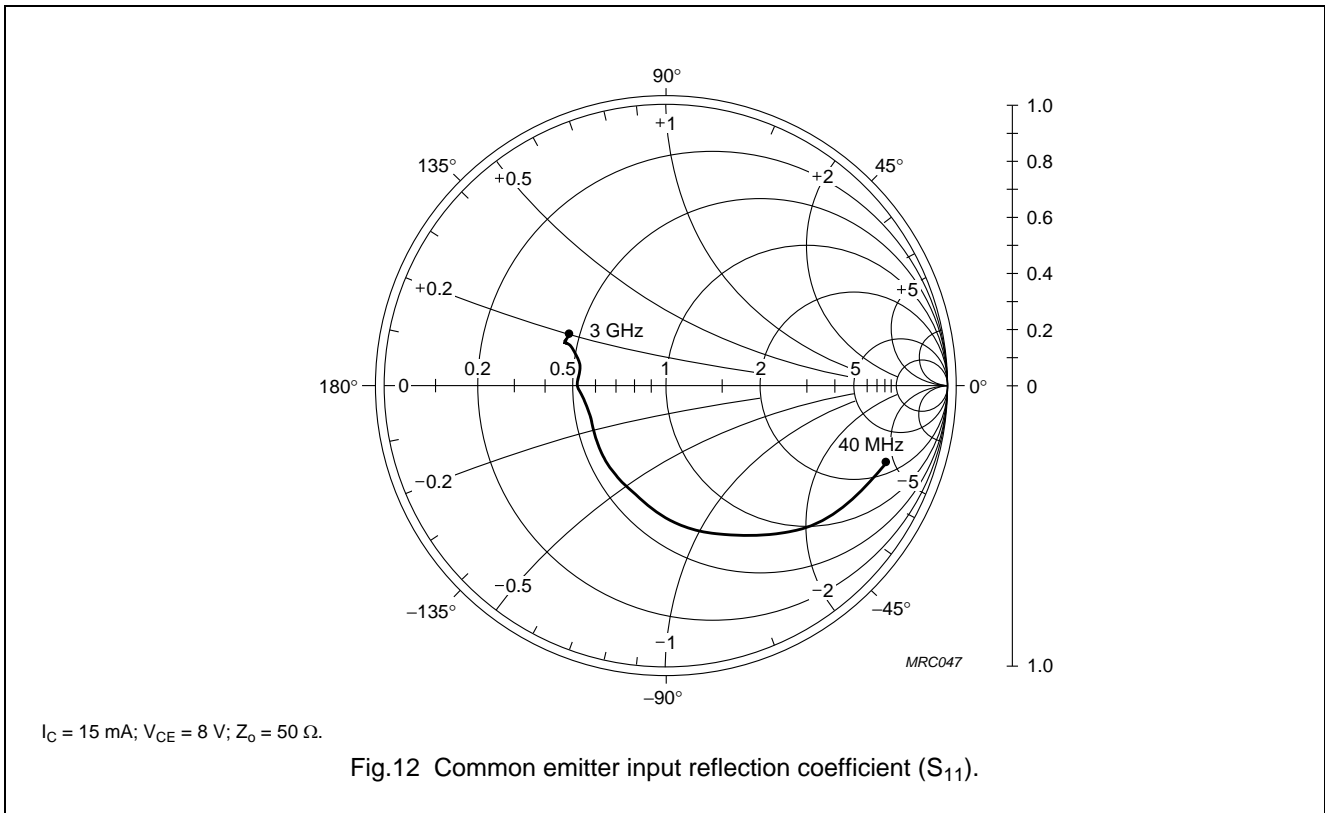
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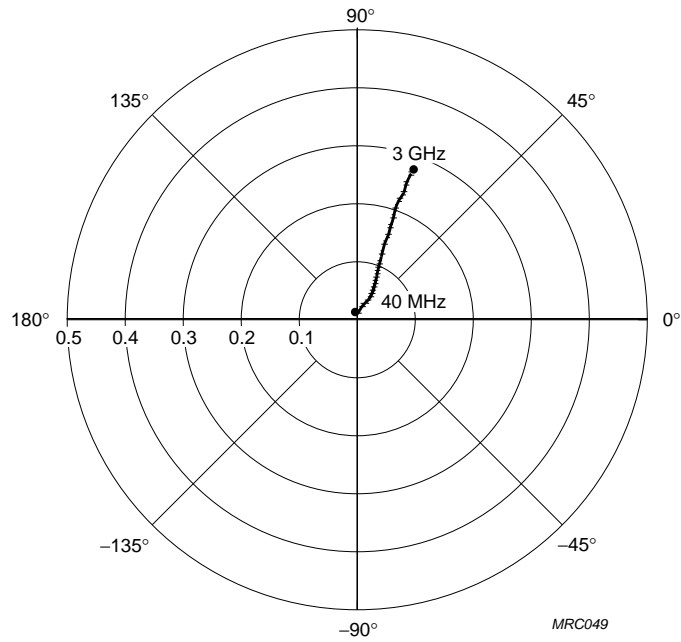
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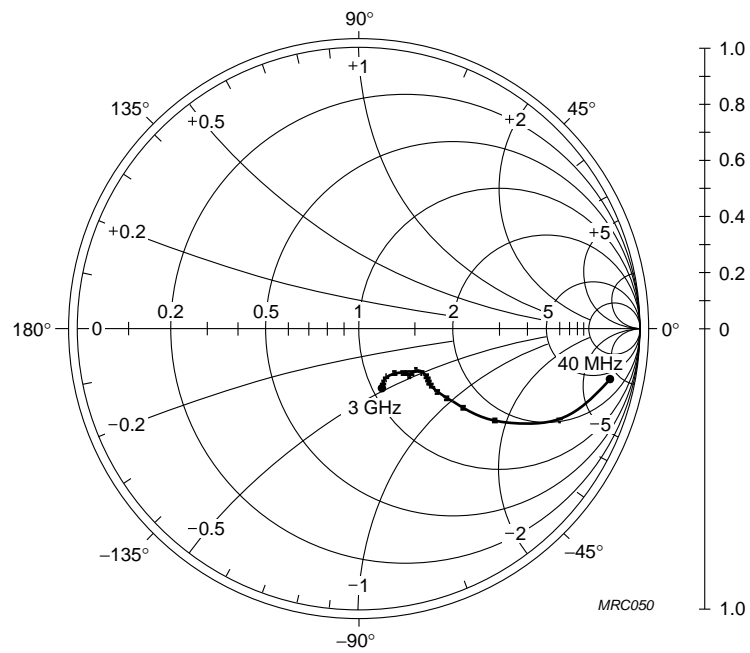
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$I_C = 15 \text{ mA}; V_{CE} = 8 \text{ V}.$

Fig.14 Common emitter reverse transmission coefficient ( $S_{12}$ ).



$I_C = 15 \text{ mA}; V_{CE} = 8 \text{ V}; Z_o = 50 \Omega.$

Fig.15 Common emitter output reflection coefficient ( $S_{22}$ ).



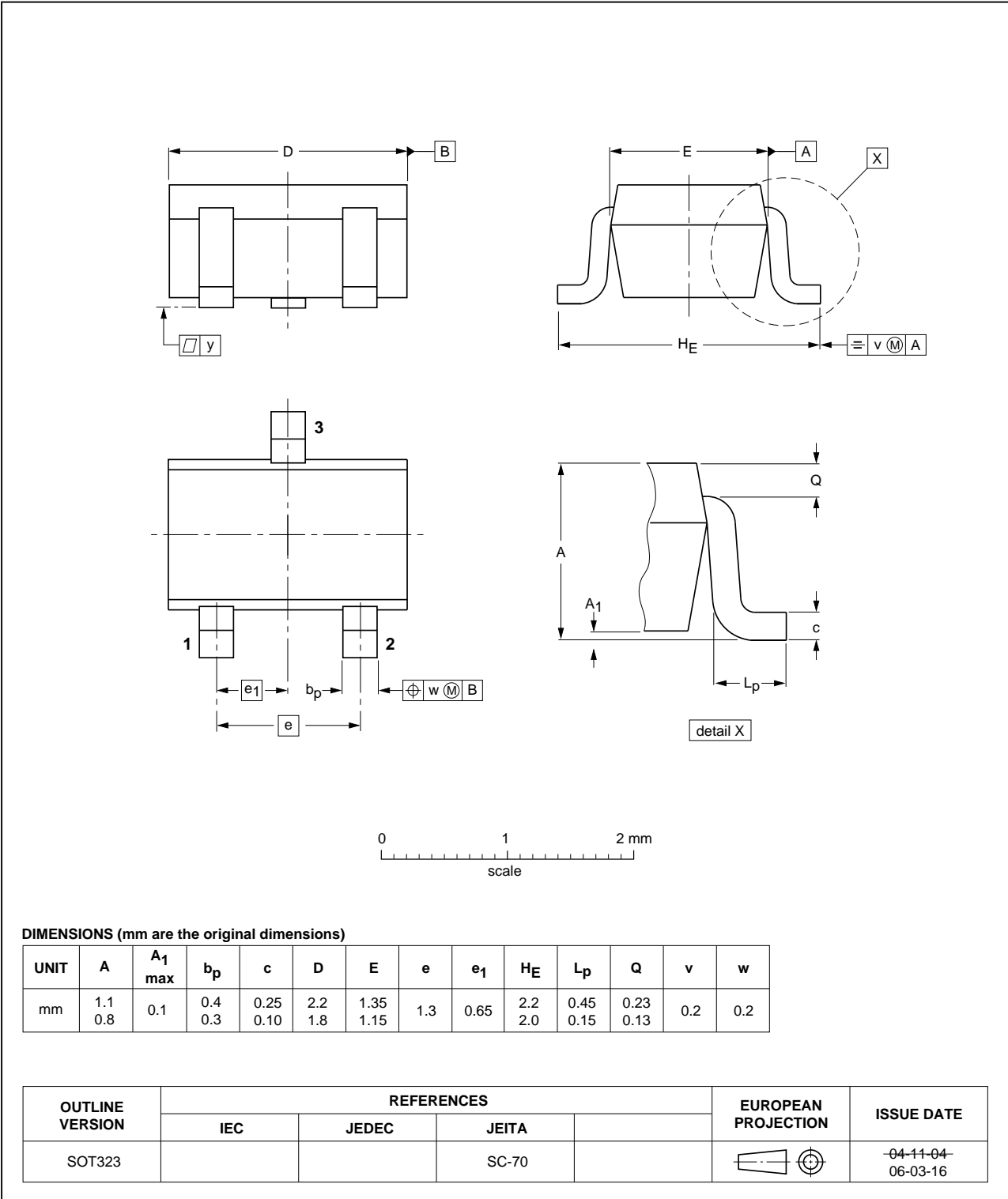
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PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT323



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## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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